# Sunday, April 17, TUTORIALS • 8 a.m. — 5:00 p.m.

| 100. Characterization | 120. Circuit Technology | 140. ESD | 150. Systems Reliability |
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| 101.<br>Wafer Level Reliability Montoring<br>A. Martin (Infineon)<br>(8:00–9:30 a.m.) | 121.<br>Mixed Signal Circuit Reliability<br>C. Schluender (Infineon)<br>(8:00–9:30 a.m.) | 141. Part 1<br>ESD & Latchup Fundamentals<br>And<br>141. Part 2<br>RF Technologies<br>S. Voldman (IBM)<br>(8:00–11:30 a.m.) | Reliability Science - It's Role in Technology Development<br>K. Seshan (Intel)<br>(8:00–9:30 a.m.) |
| 102.<br>Process Induced Damage in Advanced CMOS<br>C. Cheung (Rutgers)<br>(10:00 – 11:30 a.m.) | 122.<br>HighVoltage CMOS Device Reliability<br>P. Moens (AMI) /<br>G. Van den bosch (IMEC)<br>(10:00 – 11:30 a.m.) | | |
| **110. Reliability by Design** | **130. Failure Analysis** | | **160. High k Dielectrics** |
| 111.<br>Reliability effects in Advanced VLSI<br>W. Ellis (IBM)<br>(1:30 – 3:00 p.m.) | 131.<br>Failure Analysis Fundamentals and Advanced FA for Nanotechnology<br>C. Henderson (Semitracks)<br>(1:30 – 5:00 p.m.) | 142.<br>ESD in sub 100 nm CMOS<br>G. Boselli (TI)<br>(1:30 – 3:00 p.m.) | 161.<br>High K Gate Dielectrics Material Physics<br>G. Lucovsky (NC State)<br>(1:30 – 3:00 p.m.) |